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REPLY UNDER 37 CFR 1.116  
EXPEDITED PROCEDURE  
TECHNOLOGY CENTER 2811

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**In Re Application of:** Bruley, et al.      **Conf. #:** 2127  
**Serial No.:** 10/605,128      **Art Unit:** 2814  
**Filed:** 09/10/2003      **Docket No.:** FIS920030230US1 (JBMF-0025)  
**Title:** CAPACITOR AND FABRICATION  
METHOD USING ULTRA-HIGH  
VACUUM CVD OF SILICON NITRIDE      **Examiner:** Weiss, Howard

## COMMISSIONER FOR PATENTS

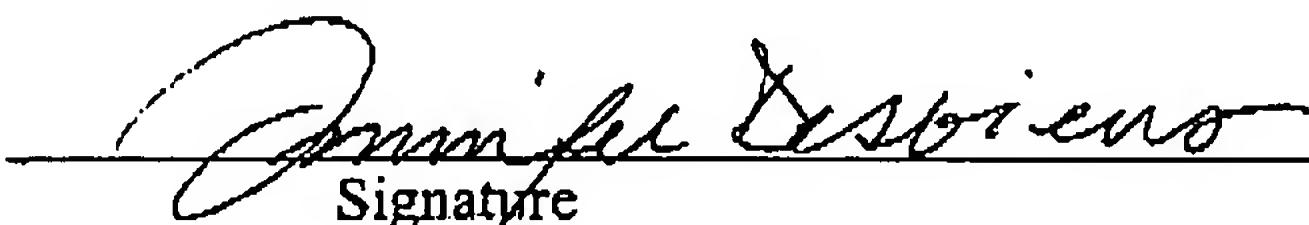
**DESTINATION FACSIMILE NUMBER:** 703-872-9306**Transmitted herewith is:** After-Final Amendment in 7 pages

in the above identified application.

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Mail Stop AF  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

## AFTER-FINAL AMENDMENT

Sir:

## I. INTRODUCTORY COMMENTS

In response to the final Office Action of January 5, 2005, please amend the above-referenced patent application as follows.

10/605,128

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